



晶体管  
TRANSISTOR  
S8050DA

### 主要参数 MAIN CHARACTERISTICS

Ic	1.5A
VCEO	45V
Pc	1W

### 产品特性 FEATURES

硅外延	Epitaxial silicon
高开关速度	High switching speed
与 S8550DA 互补	Complementary to S8550DA
RoHS 产品	RoHS product

### 用途 APPLICATIONS

高频开关电源	High frequency switch power supply
一般功率放大电路	Commonly power amplifier circuit
高频功率变换	High frequency power transform

### 封装形式 Package



1.Emitter 2.Base 3.Collector      TO-92

### 绝对最大额定值 ABSOLUTE RATINGS ( $T_c=25^\circ\text{C}$ )

项目 <b>Parameter</b>	符号 <b>Symbol</b>	数值 <b>Value</b>	单位 <b>Unit</b>
集电极—基极直流电压 Collector- Base Voltage ( $\text{IE}=0$ )	$V_{CBO}$	120	V
集电极—发射极直流电压 Collector- Emitter Voltage ( $\text{IB}=0$ )	$V_{CEO}$	45	V
发射极—基极直流电压 Emitter-Base Voltage ( $\text{IC}=0$ )	$V_{EBO}$	7	V
最大集电极直流电流 Collector Current ( DC )	$I_C$	1.5	A
最大集电极耗散功率 Total Dissipation ( TO-92 )	$P_c$	1	W
最高结温 Junction Temperature	$T_j$	150	$^\circ\text{C}$
贮存温度 Storage Temperature	$T_{stg}$	-55~+150	$^\circ\text{C}$

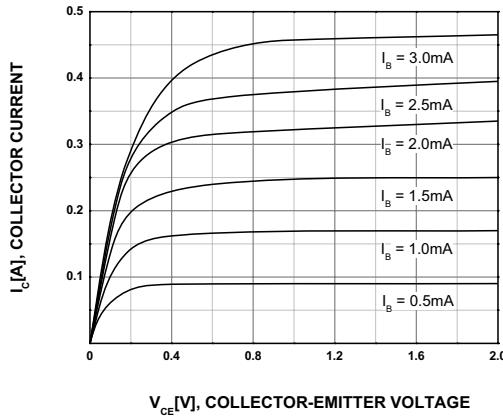
### 热特性 THERMAL CHARACTERISTIC

项目 <b>Parameter</b>	符号 <b>Symbol</b>	最小值 <b>(min)</b>	最大值 <b>(max)</b>	单位 <b>Unit</b>
结到环境的热阻 Thermal Resistance Junction Ambient	$R_{th(j-a)}$	-	125	$^\circ\text{C}/\text{W}$

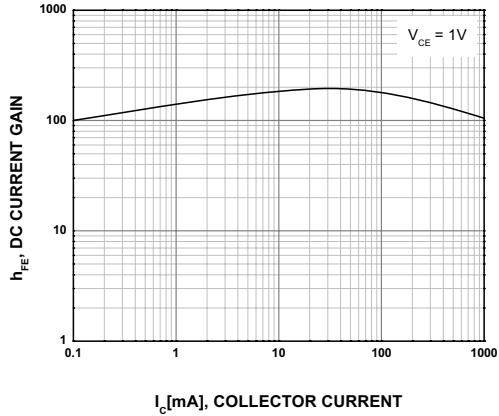
## 电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	测试条件 Tests conditions	最小值 (min)	典型值 (typ)	最大值 (max)	单位 Unit
V(BR) <sub>CBO</sub>	I <sub>c</sub> =100uA, I <sub>E</sub> =0	120	-	-	V
V(BR) <sub>CEO</sub>	I <sub>c</sub> =2mA, I <sub>B</sub> =0	45	58	-	V
V(BR) <sub>EBO</sub>	I <sub>E</sub> =100uA, I <sub>c</sub> =0	7	-	-	V
I <sub>CBO</sub>	V <sub>CB</sub> =35V, I <sub>E</sub> =0	-	-	100	nA
I <sub>EBO</sub>	V <sub>EB</sub> =6V, I <sub>c</sub> =0	-	-	100	nA
H <sub>fe</sub> (1)	V <sub>CE</sub> =1V, I <sub>c</sub> =5mA	45	-	-	
H <sub>fe</sub> (2)	V <sub>CE</sub> =1V, I <sub>c</sub> =100mA	200	-	300	
H <sub>fe</sub> (3)	V <sub>CE</sub> =1V, I <sub>c</sub> =800mA	40	-	-	
V <sub>CE(sat)</sub>	I <sub>c</sub> =800mA, I <sub>b</sub> =80mA	-	0.28	0.5	V
V <sub>BE(sat)</sub>	I <sub>c</sub> =800mA, I <sub>b</sub> =80mA	-	0.98	1.2	V
f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>c</sub> =50mA	100	-	-	MHz

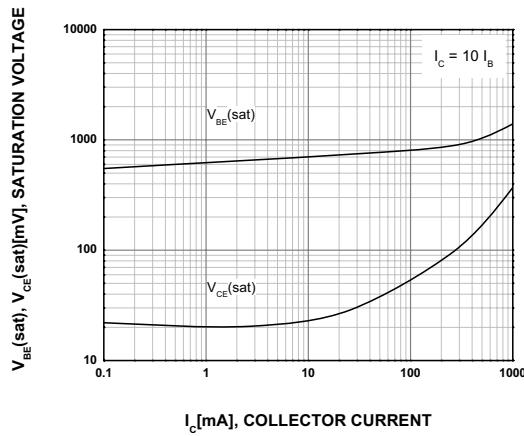
## Typical Performance Characteristics



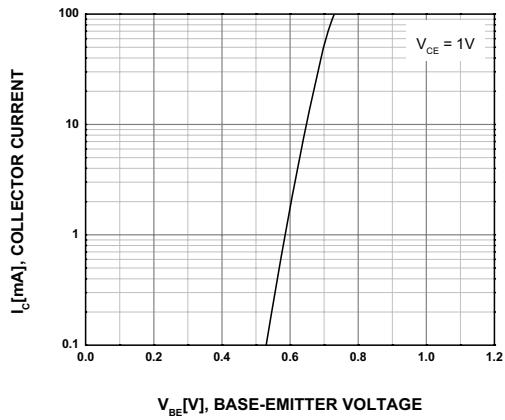
**Figure 1. Static Characteristic**



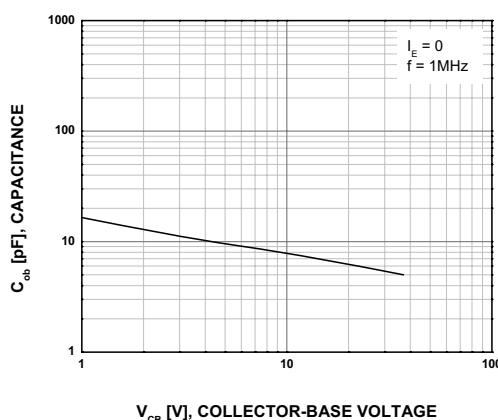
**Figure 2. DC current Gain**



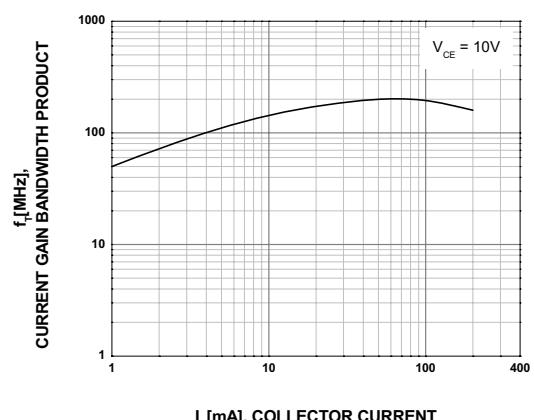
**Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage**



**Figure 4. Base-Emitter On Voltage**



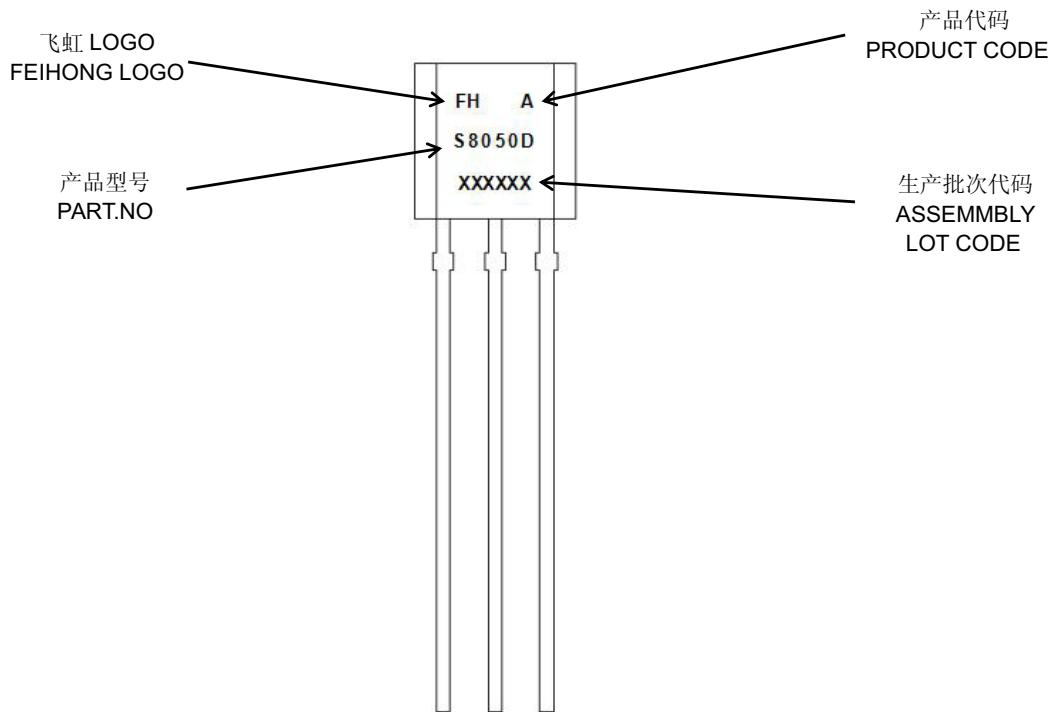
**Figure 5. Collector Output Capacitance**



**Figure 6. Current Gain Bandwidth Product**

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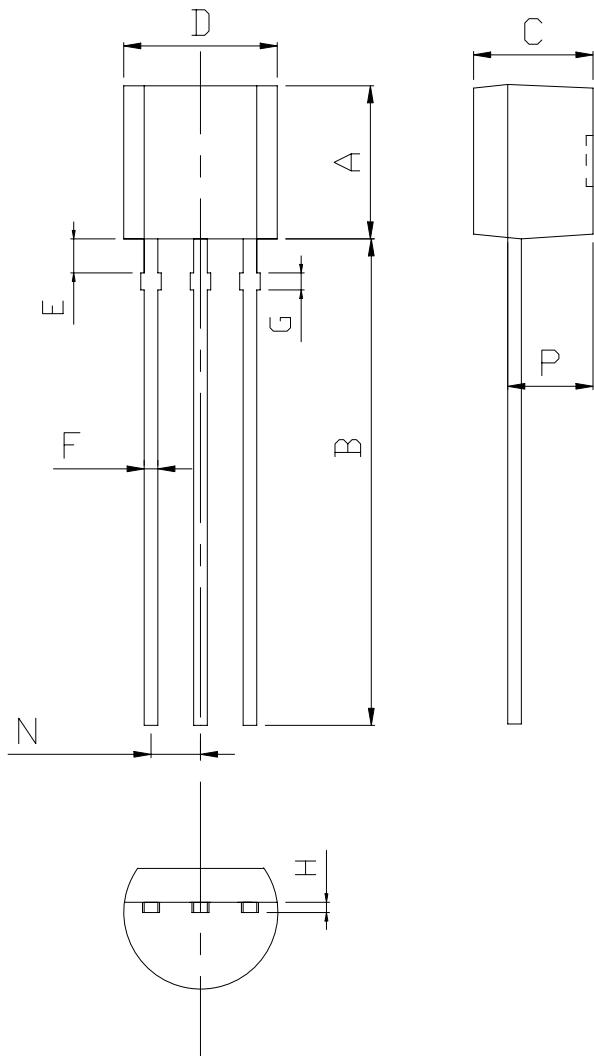
印记 Marking:



外形尺寸:

Package Dimension:

TO-92



DIM	MILLIMETERS
A	4.55+0.20
B	14.50±0.30
C	3.54±0.20
D	4.56±0.20
E	1.30±0.20
F	0.46±0.20
G	0.50±0.10
H	0.32±0.10
M	1.30±0.20
N	2.52±0.20

(Unit: mm)